

Remarks:

The cited references were considered and claims 10 and 13 were amended.

In particular, the claims were amended to avoid the indefiniteness of claim 10 and to ensure that the limitations of the preamble in claims 10 and 13 are given patentable weight. Thus claim 10 was amended to clarify the steps involved. Both claim 10 and claim 13 were also amended to explicitly include the limitation of controlling the dopant density by controlling the relative size and separation of the perforations in the mask/ the relative size and separation of the spotted implants.


This limitation is not found in any of the references. None of the references teach controlling the dopant concentration by using a mask with multiple perforations and adjusting the relative size and separation of the perforations in a mask. Similarly, none of the references teach controlling the dopant concentration in a substrate by forming spotted implants in the substrate, wherein the relative size and separation of the implants is controlled.

Furthermore, even though Yu speaks of an ESD protection device it does not teach or suggest controlling the breakdown voltage by adjusting the concentration of dopants in an isolation region formed in the substrate.

In view of the amendments to the claims, the claims are now believed to be distinguishable over all of the cited references. Early allowance of the claims is therefore respectfully requested.

Respectfully Submitted,

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